

IN THE CLAIMS:

1-43. (Cancelled)

44. (New) A method of making a semiconductor structure, comprising:

plasma etching a surface of a substrate; and

transferring heat from said substrate to (i) a seal on a support surface, and (ii) a gas in a space defined by said substrate, said seal and said support surface, uniformly across said substrate, said seal being in contact with an opposing surface of said substrate.

45. (New) The method of claim 44, wherein said substrate is held in an assembly, said assembly comprising

a holding body having said support surface, said holding body having an aperture for passing therethrough said gas, and

wherein said seal has an inner peripheral portion defining an opening for receiving said gas.

46. (New) The method of claim 45, wherein said assembly further comprises a clamp frictionally engaging said surface of said substrate.

47. (New) The method of claim 44, wherein said seal has a thickness of 25 to 125 microns.

48. (New) The method of claim 44, wherein said seal has an outer peripheral portion with a shape substantially conforming to a shape of an outer peripheral portion of said substrate.

49. (New) The method of claim 45, wherein said space is substantially airtight.

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50. (New) The method of claim 44, wherein said seal has a width of approximately 3 to 4 mm.

51. (New) The method of claim 44, wherein the substrate has a thickness of approximately 25 to 125 microns.

52. (New) The method of claim 44, wherein said gas comprises helium.

53. (New) The method of claim 44, wherein said seal comprises poly(pyromellitimido-1, 1', 4, 4',-diphenylene ether).

54. (New) A method of making a semiconductor structure, comprising:

a step for etching a surface of a substrate;

wherein said substrate is in contact with means for providing uniform heat transfer across said substrate.

55. (New) The method of claim 54, wherein said means comprises a seal, a gas and a support surface, said seal is between said substrate and said support surface, and in contact with said substrate and said support surface,

said substrate, said seal and said support surface defining a space,

said gas is in said space, and

heat transfer through said seal and said first gas provides said uniform heat transfer across said substrate.

56. (New) The method of claim 54, wherein said substrate is held in an assembly, said assembly comprising

a holding body having a support surface, said holding body having an aperture for passing therethrough a gas.

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57. (New) The method of claim 55, wherein said seal has an outer peripheral portion with a shape substantially conforming to a shape of an outer peripheral portion of said substrate.

58. (New) The method of claim 55, wherein said space is substantially airtight.

59. (New) The method of claim 55, wherein said gas comprises helium.

60. (New) A method of making a semiconductor structure, comprising:

plasma etching a surface of a substrate;

wherein said substrate has a uniform temperature.

61. (New) A method of making a semiconductor device, comprising:

making a semiconductor structure by the method of claim 44; and

making a semiconductor device comprising the semiconductor structure.

62. (New) A method of making an electronic device, comprising:

making a semiconductor device by the method of claim 61; and

making an electronic device comprising the semiconductor device.

63. (New) In a method of making a semiconductor structure, including plasma etching a substrate, wherein the substrate is on a lower electrode, and a gas is fed through the lower electrode toward the substrate, the improvement comprising a seal between the substrate and the lower electrode having a heat conductivity providing uniform heat transfer across the substrate.